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Role of domain wall fluctuations in non-Fermi liquid behavior of metamagnets

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We study resistivity temperature dependence of a three dimensional metamagnet near the metamagnet phase transition point in the case when magnetic structure tends to split into regions with high and low magnetization. We show that in the case of weak pinning the spin relaxation time of domain wall is much larger than that of the volume spin fluctuations. This opens a temperature range where resistivity temperature dependence is determined by scattering of conducting electrons by the domain wall fluctuations. We show that it leads to quasi-linear low temperature dependence of resistivity.

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I. INTRODUCTION

Understanding the deviation from the Fermi liquid behavior at phase transition critical points is a current research question. The most important are deviations from quadratic temperature dependence of resistivity near quantum critical points. Theory proposes that origin of non Fermi liquid behavior is scattering of conducting electrons by bosonic critical soft modes. In case of ferromagnetic transition these modes are collective spin excitations whose relaxation time diverges near the transition point. In nearly magnetic metals at temperatures larger than inverse spin relaxation time resistivity due to electron scattering by spin fluctuations, strongly deviates from Fermi liquid quadratic dependence. It becomes linear or even saturates.[1–4] In strongly Stoner enhanced paramagnetic metals deviation might starts at very low temperature.

It was experimentally shown that in the region near quantum critical point, magnetic state of many systems experience first order phase transition with separation of different phases.[5–14] In this case the temperature dependence of resistivity is characterized by non-Fermi liquid resistivity exponents, which depend on proximity of the system to the quantum critical point. And it was shown that dynamics of magnetic state in this case is not critical.

Nonuniform magnetic state can be considered as a distinctive phase itself.[15,16] For example in metamagnetic transition of thin magnetic films magneto-dipole interaction can give rise to formation of magnetic domains.[16] In another example domains can be formed in spatially random variation of effective magnetic field. This model was proposed to explain unusual magnetotransport effects of ferromagnetic alloys.[17]

The phase separation in first order magnetic phase transition might exists in considerable range of temperature, pressure and other parameters. In broadened phase transition the ratio of phases volume, structure and area of phase boundary depend on temperature. In broadened phase transition such factors as large difference in phases resistivity, or strong electron scattering by the phase boundary can strongly influence temperature dependence of electronic kinetic properties of material.

In this paper we consider the temperature dependence of resistivity due to scattering of conducting electrons by domain walls fluctuations in broadened metamagnetic first order phase transition. Domain walls correspond to crossover from states with low magnetization to high magnetization. Theoretically domain walls between phases appear in regions of space where two minima of free energy have equal value. The contribution to resistivity will only be significant when the wall fluctuations relaxation time is comparable or larger than that of the volume magnetic fluctuations.

The paper is organized as following. In section II we give a description of the system of coupled conducting electrons and itinerant electrons responsible for metamagnetic state. We propose a model where the magnetic state splits in to domain walls. In section III we obtain solution for the domain wall profile and consider the fluctuations around it. We then obtain dynamical magnetic susceptibility of the domain wall fluctuations. In section IV the temperature dependence of the resistivity caused by the scattering of conducting electrons by the domain wall fluctuations is considered. We find transition from quadratic to linear temperature dependence with increasing temperature. While this temperature dependence coincides with that due the volume spin-fluctuations.[3], it starts at much lower temperature. In section V we discuss the interaction correction[18] at small temperatures. It is known that conducting electrons scattering by impurities and spin fluctuations results in important contributions to the temperature dependence of conductivity.[19–22] We obtain that for domain wall fluctuations the interaction correction to conductivity has temperature dependence predicted for the 2D volume spin fluctuations.[21]

II. DESCRIPTION OF THE MODEL

We consider a three dimensional metallic metamagnet where $s-$ electrons are considered to be conducting, and $d-$ electrons responsible for the magnetic state. Coupling of conducting electrons with bosonic modes is obtained by integrating out $d-$electrons.[23] Action describing conducting electrons in random impurity potential $V(\mathbf{r})$ is

$$S_s = T\sum_{\Omega_n}\int d\mathbf{r}\,\psi^\dagger_\alpha(\mathbf{r},\Omega_n)\left[i\Omega_n+\frac{\nabla^2}{2m}+\mu-V(\mathbf{r})\right]\psi_\alpha(\mathbf{r},\Omega_n), \qquad (1)$$

where ψ describes electrons with spin α and mass m, Matsubara frequency $\Omega_n = \pi T(2n+1)$ (T is temperature), with Fermi level μ, and we have set $\hbar = 1$. We assume impurity potential to satisfy $< V(\mathbf{r}) >= 0$, and $< V(\mathbf{r})V(\mathbf{r}') >= 1/(2\pi\nu\tau)\delta(\mathbf{r}-\mathbf{r}')$, where ν - density of electrons per one spin, τ - is the electron mean free time.

The free energy of the magnetic state is described by two energetically unequal minima. Application of magnetic field brings the system in to a state at which these two minima have the same energy, this point is called metamagnetic phase transition point and the value of the magnetic field at which it occurs is called metamagnetic value of magnetic field. At the metamagnetic phase transition point we will be describing the free energy of the metamagnetic state by two parabolas with minima at $m(\mathbf{r},\tau) = \pm m_0$, corresponding to high and low magnetization states. In this case the domain walls originate from the spatial deviation of the magnetic field from its metamagnetic value, and we introduce such deviation as $h(\mathbf{r})$ (see figure 1). Assuming strong magnetic field we only consider longitudinal component of magnetization density $m(\mathbf{r})$ (in units of $g\mu_B \equiv 1$) in the action. Having above assumptions in hand we write the action describing the magnetization density $m(\mathbf{r},\tau)$ in the form

$$\begin{aligned} S_{mag}[m] = \int_0^{1/T} d\tau \int d\mathbf{r} \Big(&\tfrac{K}{2\chi_0}\left(\nabla m\left(\mathbf{r},\tau\right)\right)^2 \\ &+ \tfrac{\alpha}{2\chi_0}\left(\left|m\left(\mathbf{r},\tau\right)\right| - m_0\right)^2 - h\left(\mathbf{r}\right)m\left(\mathbf{r},\tau\right)\Big) + S_D, \end{aligned} \qquad (2)$$

here coefficient $K^{-1/2}$ is of the order of electrons Fermi wave length, α^{-1} is a Stoner enhancement factor, and χ_0 is conducting electron spin susceptibility which we have assumed to be equal for both high and low magnetization phases. This assumption greatly simplifies further calculations, and does not affect main conclusions about resistivity temperature dependence. We assume the spatial distribution of the $h(\mathbf{r})$ to be of the Gaussian form and give the averaging procedure in the appendix.

The last term in (2) is the Landau damping described by

$$S_D[m] = \int d\mathbf{r}' d\mathbf{r}\; T\sum_{\omega_n} m\left(\mathbf{r},\omega_n\right)\Gamma(\mathbf{r}-\mathbf{r}',\omega_n) m\left(\mathbf{r}',\omega_n\right), \qquad (3)$$

here ω_n is the bosonic Matsubara frequency. At this point it is necessary to distinguish two cases of the form of the damping. When the scattering of conducting electrons by impurities is ballistic the Fourier image of Γ is given by $\Gamma(\mathbf{Q},\omega_n) = \frac{\gamma|\omega_n|}{v_F Q}$, which is valid for large momenta $v_F Q > |\omega_n|$ where v_F is Fermi velocity, and γ is a damping constant.[3,24] In case of diffusive scattering the damping is $\Gamma(\mathbf{Q},\omega_n) = \frac{\gamma|\omega_n|}{DQ^2}$ which is valid for $DQ^2 > |\omega_n|$ where D is the diffusion constant.[25]

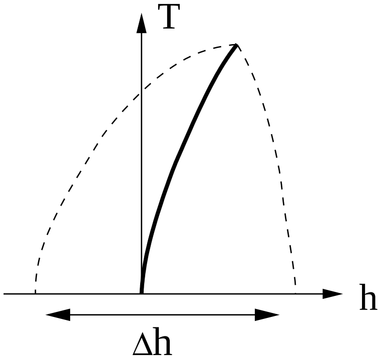

FIG. 1: Schematic phase diagram of the broadened first order phase transition. The solid curve shows putative transition, while area enclosed by dashed curves represents the phase separated state.

Finally, action describing coupling of conducting electrons with magnetization is

$$S_{int} = G\int_0^{1/T} d\tau \int d\mathbf{r}\; s\left(\mathbf{r},\tau\right) m\left(\mathbf{r},\tau\right), \qquad (4)$$

here $\mathbf{s}\left(\mathbf{r},\tau\right)$ is operator of spin density of conducting electrons along the longitudinal component of magnetization, G is a phenomenological coupling constant.

III. DOMAIN WALL FLUCTUATIONS

In this section we give a solution to the mean field equation for the domain wall and discuss fluctuations around this solution. Let x be a coordinate normal to the domain wall and $h\left(x_0(\boldsymbol{\rho})\right) = 0$, so that at $x < x_0$ it is state with high magnetization, and at $x > x_0$ it is a low magnetization state. Here $\boldsymbol{\rho}$ is a 2D coordinate along the two dimensional domain wall. Equation for magnetization is obtained by varying the action (2) and we get

$$-K\frac{d^2}{dx^2}m + \alpha\left(m - m_0 sign(m)\right) = \chi_0 h(x). \qquad (5)$$

When $h(\mathbf{r})$ is slowly varying function on a scale of $\sqrt{K/\alpha}$ the domain wall can be approximated as flat. With this assumption the solution of (5) describing the domain wall is

$$m = -m_0(1-e^{-\sqrt{\alpha/K}|x-x_0(\boldsymbol{\rho})|})sign(x-x_0(\boldsymbol{\rho})) + \frac{\chi_0 h(x)}{\alpha}. \qquad (6)$$

Let us consider fluctuations near this solution. Taking second derivative of free energy we obtain equation for eigenfunctions, which describe fluctuations

$$\begin{aligned} &(-K\nabla^2+\alpha)\delta m(\mathbf{r}) \\ &-\frac{2\alpha m_0}{\left|\frac{d}{dx}(m(x))\right|_{x=x_0}}\delta(x-x_0(\boldsymbol{\rho}))\delta m(\mathbf{r}) = \epsilon\delta m(\mathbf{r}). \end{aligned} \qquad (7)$$

Deriving this equation we have used the equality

$$\delta(m(x)) = \frac{\delta(x - x_0(\boldsymbol{\rho}))}{\left|\frac{d}{dx}(m(x))\right|_{x=x_0}}. \tag{8}$$

δ type potential in equation (7) is related to non analytical dependence of free energy on magnetization. The equation (7) has only one bounded solution, thus strongly simplifying consideration of fluctuations. At slowly varying $x_0(\boldsymbol{\rho})$ and $\frac{d}{dx}m(x_0(\boldsymbol{\rho}))$ one can search for the solution of equation (7) in the form of a plane wave in $\boldsymbol{\rho}$

$$\delta m(r) = \Psi_0(x - x_0(\boldsymbol{\rho}))e^{i\mathbf{Q}\boldsymbol{\rho}}, \tag{9}$$

where

$$\Psi_0(x) = \sqrt{\beta}e^{-\beta|x-x_0|}, \tag{10}$$

and assuming $\epsilon = KQ^2 + \epsilon_0$ we find

$$\epsilon_0 = \alpha\left[1 - \left(1 + \frac{\chi_0}{m_0\sqrt{K\alpha}}\left|\frac{d}{dx}h(x)\right|\right)^{-2}\right], \tag{11}$$

where $\beta = \sqrt{(\alpha - \epsilon_0)/K}$. At slowly varying $h(\mathbf{r})$ we find that $\epsilon_0 << \alpha$ and we approximate $\beta = \sqrt{\alpha/K}$. In this case

$$\epsilon_0 = \frac{2\chi_0}{m_0\beta}\left|\frac{d}{dx}h(x)\right|. \tag{12}$$

Dynamics of spin fluctuations is governed by the Landau damping (3) which for excitation described by $\Psi_0(x)$ translates to

$$\gamma(Q) = \frac{\gamma}{v_F}\int_{-\infty}^{\infty} dx dx' \Psi_0(x)\Psi_0(x')\int_{-\infty}^{\infty} dq \frac{e^{iq(x-x')}}{\sqrt{Q^2+q^2}}, \tag{13}$$

where as an example we used ballistic case. At small momenta $\beta > Q$ we have for the ballistic case

$$\gamma(Q) = \frac{4\gamma}{\pi\beta v_F}\ln(\beta/Q). \tag{14}$$

Same procedure for the diffusive case gives

$$\gamma(Q) = \frac{2\gamma}{DQ\beta}. \tag{15}$$

The dynamical susceptibility of one domain wall fluctuations is represented in the form

$$\chi(\mathbf{r}, \mathbf{r}', \omega) = \int \frac{d^2Q}{(2\pi)^2} e^{-i\mathbf{Q}(\boldsymbol{\rho}-\boldsymbol{\rho}')}\Psi_0(x)\Psi_0(x')\chi(\mathbf{Q}, \omega), \tag{16}$$

where

$$\chi(\mathbf{Q}, \omega) = \frac{\chi_0}{\epsilon_0 + KQ^2 + i\omega\gamma(Q)}. \tag{17}$$

We consider a locally flat domain boundary. This can be justified if scale along wall $L_{\parallel} \sim \sqrt{\frac{K}{\epsilon_0}} \sim \frac{1}{p_F\sqrt{\epsilon_0}}$ is much smaller than domain wall curvature. Typical scattering of conducting electrons by fluctuations of the domain wall is characterized by the momentum of the order of β. Which is much larger than the momentum of the dynamical susceptibility of fluctuations. This allows to separately average over the domain wall direction and position, introducing concentration of wall n_W. The average over random ϵ_0 is approximated by substituting the average value of ϵ_0 in to the susceptibility. The details of the described above averaging steps are given in the appendix to the paper.

From (17) we see that relaxation time of domain wall fluctuations is proportional to ϵ_0^{-1} which is much larger than that of the volume fluctuations since $\epsilon_0 << \alpha$. At small ϵ_0 contribution of the domain wall fluctuations to the total susceptibility of the system is approximately

$$\delta\chi_0 \sim n_W \int dx dx' \Psi_0(x)\Psi_0(x')\chi(0,0) \sim \frac{\chi_0 n_W}{\beta\epsilon_0}, \tag{18}$$

which can be of the same order as χ_0 depending on the parameters.

IV. RESISTIVITY TEMPERATURE DEPENDENCE

Let us consider contribution to the resistivity due to domain wall scattering of conducting electrons. There are three temperature dependent contributions to the conductivity. They are due to scattering of conducting electrons by fluctuations of domain wall, due to domains walls shape change when temperature increases, and due to variation of concentration of walls n_W. First two contributions are considered in this section and have a common nature. Third contribution depends on position on the phase diagram. We discuss its contribution in the conclusions of the paper.

Resistivity due to electron scattering by spin fluctuation is obtained in second order perturbation theory in interaction (4) and is expressed through imaginary part of averaged susceptibility as[2,3]

$$\rho(T) = R_0\frac{1}{T}\int_0^{2p_F}\frac{dq q^3}{p_F^4}\int_{-\infty}^{\infty}\frac{d\omega\omega}{\sinh^2(\omega/2T)}\operatorname{Im}\chi(\mathbf{q}, \omega), \tag{19}$$

here

$$R_0 = \frac{mG^2\nu}{32e^2n}, \tag{20}$$

where ν is density of states of conducting electrons per spin, p_F, n, m are Fermi momentum, density, and mass of conduction electrons respectively.

In addition the fluctuations give temperature dependent contribution to the average magnetization of wall. Fluctuation part of magnetization is determined by derivative $\delta m(\mathbf{r}) = -\frac{\delta\Delta\Omega}{\delta h(\mathbf{r})}$ of fluctuation part of the free energy $\Delta\Omega = \frac{1}{2}T\sum_{\omega_n,Q}\ln(\epsilon_Q + \gamma(Q)\omega_n)$. This leads to a change of the domain wall profile and gives additional temperature dependence of resistivity proportional to $G^2 m(\mathbf{Q})\delta m(\mathbf{Q},T)$. Sum of both contributions to the resistivity is given by

$$R = \tfrac{4\pi\beta R_0 n_W}{p_F^4}\int\limits_0^\infty d\omega\left(\tfrac{\omega}{T\sinh^2(\omega/2T)} - 2\coth(\tfrac{\omega}{2T}) + 2\right) \int \tfrac{d^2Q}{(2\pi)^2}\,\mathrm{Im}\,\chi(\mathbf{Q},\omega). \tag{21}$$

Term, proportional to $(-\coth(\frac{\omega}{2T}) + 1)$, is due to $\delta m(\mathbf{Q},T)$.

Our calculations show that despite of the difference in damping in ballistic (14) and diffusive (15) regimes the temperature dependence of resistivity has the same form for both of the cases. It is quadratic at temperatures lower than the inverse relaxation time and linear at larger temperature. We get that in the ballistic scattering regime at temperatures $T < T_0$ resistivity has quadratic temperature dependence

$$R = \frac{2\pi\beta R_0 n_W \chi_0}{p_F^4}\frac{T^2}{KT_0}, \tag{22}$$

and at temperatures $T > T_0$ the dependence is linear

$$R = \frac{2\pi\beta R_0 n_W \chi_0}{p_F^4}\frac{T}{K}, \tag{23}$$

here $T_0 = \beta v_F \epsilon_0/(5\ln(\beta^2 K/\epsilon_0))$. In case of diffusive scattering regime we get that the resistivity dependence of the temperature has the same form with T_0 modified as $T_0 \equiv D\beta\epsilon_0\sqrt{K/\epsilon_0}$. The transition from quadratic T^2 to linear T dependence corresponds to transition from quantum to thermal fluctuations of domain wall.[26]

We would like to notice that the same temperature dependence holds for scattering by volume spin fluctuations, except for the difference of effective T_0 in ballistic and diffusive cases.[24,25] Let us compare resistivity temperature dependence (22) and that $\varrho_{vol}(T)$ due to volume spin fluctuations. In the considered temperature range the volume contribution is quadratic and $\varrho_{vol}(T) \sim R_0\chi_0 T^2/(p_F v_F\sqrt{\alpha})$.[2,3] Ratio $R(T)/\varrho_{vol}(T) \sim \frac{n_W}{p_F\epsilon_0}$ can be of order of one.

V. INTERACTION CORRECTION

At low temperatures important resistivity temperature dependence is related to weak localization and electron interaction corrections.[18] Here we are going to discuss contribution to the conductivity originating from the interplay between electron inelastic scattering by domain wall fluctuations and elastic scattering by impurities. The triplet channel contribution to the conductivity after disorder averaging is given by[21,27]

$$\delta\sigma = 2\pi e^2 v_F^2 \tau\nu G^2 \int \tfrac{d\omega}{4\pi^2}\left[\tfrac{\partial}{\partial\omega}\left(\omega\coth\tfrac{\omega}{2T}\right)\right] \times \mathrm{Im}\int \tfrac{d^3q}{(2\pi)^3} B(\mathbf{q},\omega)\chi(\mathbf{q},\omega), \tag{24}$$

here we also averaged over the positions of the domain walls after which the equation above became isotropic. In the ballistic regime $T\tau > 1$ one can use the following approximation $B(\mathbf{q},\omega) \approx 2/(v_F q)^2$ which is valid for $v_F q > |\omega|$, and the expression for the domain wall profile fluctuations propagator at small momenta $q < \beta$ is $\chi(\mathbf{q},\omega) = 4n_W\chi_0/\beta\left(\epsilon_0 + KQ^2 + i(4\gamma\omega/(\pi v_F\beta))\ln\left(\alpha/KQ^2\right)\right)^{-1}$. We only consider temperature dependent terms of the correction.

We find that at temperatures $T > \pi v_F\beta\epsilon_0/(2\gamma) \simeq T_0$ and $T < v_F\sqrt{\epsilon_0/K}$ the correction to the conductivity is logarithmic in temperature

$$\delta\sigma = -\left(\frac{\chi_0}{2\pi^2\gamma}e^2\nu G^2 n_W\right)\sqrt{\epsilon_0/K}\,v_F\tau\ln\left(\frac{\sqrt{\epsilon_0/K}\,v_F}{T}\right). \tag{25}$$

At higher temperatures $T > v_F\sqrt{\epsilon_0/K}$ and $T < \frac{2v_F\gamma}{\pi K\beta}$ the correction to the conductivity is linear

$$\delta\sigma = \left(\frac{5\chi_0}{12\pi^2\gamma}e^2\nu G^2 n_W\right)\tau T. \tag{26}$$

At higher temperatures the correction decays as $1/T$.

Now let us discuss the diffusive regime at $T\tau < 1$. In this case $B(\mathbf{q},\omega) = \frac{4}{3}\frac{Dq^2}{(Dq^2+i\omega)^3}$ and $\chi(\mathbf{q},\omega) = 4n_W\chi_0/\beta\left(\epsilon_0 + KQ^2 + i2\gamma\omega/(D\beta Q)\right)^{-1}$ approximated at small momenta $q < \beta$. Most singular contribution arises from $\sqrt{|\omega|/D} < q < \min(\beta, 1/\ell)$, and $q > \sqrt{\epsilon_0/K}$. Where ℓ is the electron‘s mean free path. Calculations show that at temperatures $p = \min(\Omega_1, \Omega_2, 1/\tau) > T$, where $\Omega_1 = \frac{\gamma^2 D}{2K^2\beta^2}$, $\Omega_2 = \sqrt{2}\beta^4 DK/\gamma$ the contribution to the conductivity is

$$\delta\sigma = -\left(\frac{2^{7/2}\chi_0}{9\pi^3\gamma}e^2\nu G^2 n_W\right)\ln\left(\frac{p}{T}\right)\ln\left(\frac{pT}{\Omega_1^2}\right). \tag{27}$$

We would like to point out that we have not considered all of the possible regimes of parameters, focusing on the most interesting cases. Expressions (25), (26), and (27) have a 2D temperature behavior while obtained for the 3D electron system.[21] The resistivity correction is obtained by $\delta\rho = 1/\sigma_D(1 - \delta\sigma/\sigma_D)$, where σ_D is the Drude conductivity.

VI. CONCLUSION

We considered the temperature dependence of resistivity due to electron scattering by spin fluctuations of domain walls. We showed that in case of weak pinning $\alpha >> \epsilon_0$ the relaxation of domain wall fluctuations is much slower than relaxation of volume spin density. Therefore, classical regime of fluctuations characterized by linear temperature dependence starts at much lower temperature than for the volume fluctuations. In considered temperature range contribution of volume fluctuations to resistivity is always $\sim T^2$.

It is reasonable to assume, that additional resistivity in considered system is proportional to n_w. Depending on relation between average magnetic field and metamagnetic $h_m(T)$ the concentration n_w can change with the temperature. In considered temperature range the concentration changes with the temperature as $n_W(T) = n_W(0)(1 + a(T\tau_S)^2)$, where $|a| \sim 1$ and the sign of a depends on the average magnetic field. The $\tau_S \sim 1/(\alpha p_F v_F)$ is relaxation time of volume fluctuations. Parameter $T\tau_S$ determines renormalization of free energy due to volume spin fluctuations.[3] For example in schematic phase diagram shown in fig. 1 the n_W decreases in the region $h < 0$ when $h_m(T)$ increases with temperature.

In case when $a < 0$ there can be a cancelation of quadratic temperature dependence of volume contribution to resistivity by the contribution of domain walls $n_W(T)$. In case of the cancelation, obtained results (23), (25), and (26) will be dominant. And the total resistivity will have quasi-linear non-Fermi liquid temperature dependence.

Acknowledgments

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Appendix A: Averaging over random surfaces

Here we show the averaging procedure over the direction of domain walls and random ϵ_0. We assume that magnetic field is described by Gaussian distribution such that

$$\langle \Delta h(\mathbf{r}) \Delta h(\mathbf{r}') \rangle = A \exp(-\zeta(\mathbf{r} - \mathbf{r}')^2) \tag{A1}$$

and $\langle \Delta h(\mathbf{r}) \rangle = 0$, where $\Delta h(\mathbf{r}) = h(\mathbf{r}) - h_0$. When parameter ζ is small the magnetic field becomes a slowly varying random function $h(\mathbf{r})$. Typical phase boundary in such a random field is smooth. Position of domain wall is defined by the following equation

$$h(\mathbf{r}) = h_0 + \Delta h(\mathbf{r}) = 0 \tag{A2}$$

Note, that under this definition we neglect cases when in small closed regions there is no solution of mean field equation (5) for favorite phase, or energy associated with it is too high.

Fourier transform of any quantity $V(\mathbf{r})$ which is nonzero near the domain wall surface and slowly varying along it, is calculated as

$$V(\mathbf{q}) = \int d\mathbf{r} \ \exp(i\mathbf{q}\mathbf{r}) V(\mathbf{r}) = \int dS \ \exp(i\mathbf{q}\mathbf{r}_S) V(\mathbf{q}\mathbf{n}(\mathbf{r}_S), \mathbf{r}_S) = \int d\mathbf{r} \ V(\mathbf{q}\mathbf{n}(\mathbf{r}), \mathbf{r}) \exp(i\mathbf{q}\mathbf{r}) |\frac{d}{d\mathbf{r}} h(\mathbf{r})| \delta(h(\mathbf{r})), \tag{A3}$$

here $\mathbf{r}_S$ is a point on the surface, and $\mathbf{n}(\mathbf{r}_S)$ is a vector normal to the surface at the point $\mathbf{r}_S$ defined as $\mathbf{n}(\mathbf{r}) = \frac{dh(\mathbf{r})}{d\mathbf{r}} / |\frac{d}{d\mathbf{r}} h(\mathbf{r})|$. In (A3) $V(\mathbf{q}\mathbf{n}(\mathbf{r}), \mathbf{r})$ is a one dimensional Fourier transform in the direction normal to the surface.

We now can average the dynamical susceptibility of the number of domain wall. For one domain wall the susceptibility is given by expression (16). Scale along the surface of the domain wall that we are interested in is $L_\parallel \sim \sqrt{\frac{K}{\epsilon_0}} \sim \frac{1}{p_F \sqrt{\epsilon_0}}$, here $\delta h \sim \sqrt{A} \sim \frac{\alpha m_0}{\chi_0}$ and the ϵ_0 is estimated as

$$\epsilon_0 \sim \frac{\chi_0}{m_0 \sqrt{\alpha/K}} |\frac{dh}{dx}| \sim \sqrt{\alpha K} \sqrt{\zeta}. \tag{A4}$$

Therefore $L_\parallel \sim \frac{1}{p_F} \sqrt{\beta/\alpha\sqrt{\zeta}}$ is smaller than the radius of surface curvature $L_\parallel \sqrt{\zeta} \sim \sqrt{\sqrt{\zeta}/\beta} << 1$, and under averaging procedure we can use the expression (16). Then the average susceptibility is

$$\chi(\mathbf{q}, \omega) = \int d^3\mathbf{R} \int d\mathbf{b} \Pi(\mathbf{R}, \mathbf{b}) \exp(i\mathbf{q}\mathbf{R}) \mathbf{b}^2 \Psi_0(\mathbf{q}\mathbf{n}) \Psi_0(-\mathbf{q}\mathbf{n}) \int \frac{d^2Q}{(2\pi)^2} \exp(i\mathbf{Q}\mathbf{R}) \chi(\mathbf{Q}, \omega), \tag{A5}$$

where $\Psi_0(q) = 2\beta^{3/2}/(q^2 + \beta^2)$ is a Fourier transform of $\Psi_0(x)$ defined by (10), and

$$\Pi(\mathbf{r}_1 - \mathbf{r}_2, \mathbf{b}) = \langle \delta(h(\mathbf{r}_1)) \delta(h(\mathbf{r}_2)) \delta(\mathbf{b} - \frac{1}{2}(\frac{d}{d\mathbf{r}_1} h(\mathbf{r}_1) + \frac{d}{d\mathbf{r}_2} h(\mathbf{r}_2))) \rangle. \tag{A6}$$

At $R << \sqrt{\zeta}$ the $\mathbf{b}$ is a normal to the surface and therefore is also normal to $\mathbf{R}$. Therefore in (A5) we can separately average over the direction and value of $\mathbf{b}$, considering $\Pi(\mathbf{R}, \mathbf{b})$ only in the limit of $R\sqrt{\zeta} << 1$. In case of Gaussian distribution $\Pi(\mathbf{R}, \mathbf{b})$ is calculated analytically as

$$\Pi(\mathbf{R}, \mathbf{b}) = \frac{n_W}{16RA\zeta} P(\mathbf{b}_\perp) P(\mathbf{b}_\|), \tag{A7}$$

where

$$P(\mathbf{b}_\perp) = \frac{1}{2\pi A\zeta} \exp(-\frac{\mathbf{b}_\perp^2}{2A\zeta}) \tag{A8}$$

and

$$P(\mathbf{b}_\|) = \sqrt{\frac{3}{\pi A\zeta^3 R^4}} \exp(-\frac{3\mathbf{b}_\|^2}{A\zeta^3 R^4}), \tag{A9}$$

here $\mathbf{b}_\perp$ and $\mathbf{b}_\|$ are perpendicular and parallel components to $\mathbf{R}$ consequently. The quantity n_W has a meaning of the domain wall concentration and is defined as

$$n_W \equiv \frac{\langle \int d\mathbf{r} \delta(h(\mathbf{r})) |\frac{d}{d\mathbf{r}} h(\mathbf{r})| \rangle}{V} = \frac{\sqrt{8\zeta}}{\pi} \exp(-\frac{h_0^2}{A}) \tag{A10}$$

where V is the volume of the system. The factor $\mathbf{b}^2$ under the integral of expression (A5) is estimated as $\mathbf{b}^2 \sim \epsilon_0^2$. So averaging of quantities like susceptibility does not diverge at small ϵ_0 and can be approximated by inserting average ϵ_0. Finally, the averaged susceptibility over the domain wall positions is given by the next expression:

$$\chi(\mathbf{q}, \omega) = \frac{1}{4\pi} \int d^2\mathbf{n} \Psi_0(\mathbf{qn}) \Psi_0(-\mathbf{qn}) \frac{n_W \chi_0}{\epsilon_0 + K\mathbf{Q}^2 + i\omega\gamma(\mathbf{Q})}, \tag{A11}$$

where ϵ_0 is approximated by its average value. At small momenta $q < \beta$ Fourier transform $\Psi_0(\mathbf{qn})$ is approximated as $\Psi_0 = 2/\sqrt{\beta}$.

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